

# UNISONIC TECHNOLOGIES CO., LTD

**UTD454 Power MOSFET** 

# N-CHANNEL ENHANCEMENT MODE POWER MOSFET

#### **DESCRIPTION**

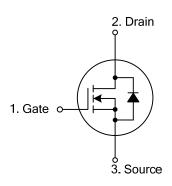
The UTC UTD454 is an N-channel enhancement MOSFET providing perfect  $R_{\text{DS}(\text{ON})}$  and low gate charge with UTC advanced technology.

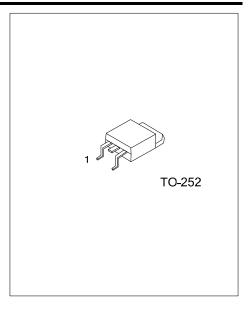
The UTC UTD454 is intended for being used in PWM, load switching and general purpose applications.

#### **FEATURES**

- \*  $R_{DS(ON)}$ < 33 m $\Omega$  @ $V_{GS}$  = 10V
- \*  $R_{DS(ON)}$ < 47 m $\Omega$  @ $V_{GS}$  = 4.5V
- \*  $V_{DS}(V) = 40V$
- \*  $I_D$  = 12 A @ $V_{GS}$  = 10V
- \* Low gate charge

#### **SYMBOL**

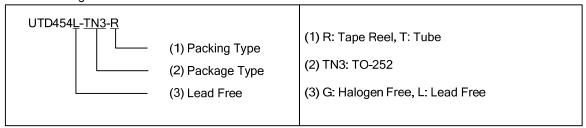




### ORDERING INFORMATION

Ordering Number		Dankana	Pin Assignment			Da alsia si	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTD454L-TN3-R	UTD454G-TN3-R	TO-252	G	D	S	Tape Reel	
UTD454L-TN3-T	UTD454G-TN3-T	TO-252	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



UTD454

# **Power MOSFET**

# ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current (T <sub>C</sub> =25°C)	I <sub>D</sub>	12	Α
Pulsed Drain Current (Note 2)	I <sub>DM</sub>	30	Α
Avalanche Current (Note 2)	I <sub>AR</sub>	12	Α
Repetitive avalanche energy (L=0.1mH)(Note 2)	E <sub>AR</sub>	20	mJ
Power Dissipation (T <sub>C</sub> =25°C)	$P_{D}$	20	W
Junction Temperature	TJ	+150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

# ■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	60	°C/W
Junction to Case	$\theta_{ m JC}$	3	°C/W

Note: Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board with 2oz

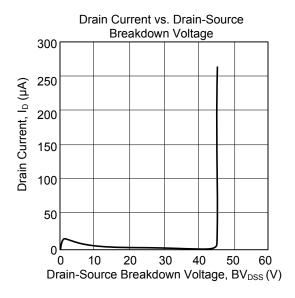
# ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

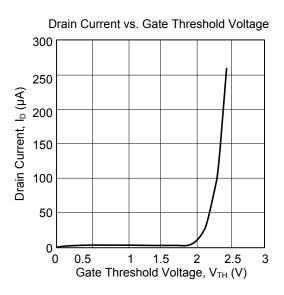
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	40			V	
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V			1	μΑ	
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ =0V, $V_{GS}$ =±20V			±100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$ $V_{DS}=V_{GS}$ , $I_D=250\mu A$		1.8	2.3	3	V	
On-State Drain Current	$I_{D(ON)}$	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V				Α	
Drain to Source On-state Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =12A		25	33	mΩ	
Diam to Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A		34	47	mΩ	
DYNAMIC PARAMETERS							
Input Capacitance	C <sub>ISS</sub>			404	500	pF	
Output Capacitance	Coss	V <sub>GS</sub> =0V, V <sub>DS</sub> =20V, f=1MHz		95	150	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>			37	60	nC	
Gate resistance	$R_{G}$	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		2.7		Ω	
SWITCHING PARAMETERS							
Turn-ON Delay Time	t <sub>D(ON)</sub>			3.5		ns	
Turn-ON Rise Time	t <sub>R</sub>	$V_{GS}$ =10V, $V_{DS}$ =20V, $R_L$ =1.7 $\Omega$ ,		6		ns	
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	$R_{GEN}$ =3 $\Omega$		13.2		ns	
Turn-OFF Fall-Time	t <sub>F</sub>			3.5		ns	
Total Gate Charge	$Q_{G}$			9.2		nC	
Gate Source Charge	$Q_{GS}$	V <sub>GS</sub> =10V, V <sub>DS</sub> =20V, I <sub>D</sub> =12A		1.6		nC	
Gate Drain Charge	$Q_{GD}$			2.6		nC	
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.76	1	V	
Diode Continuous Forward Current	Is				12	Α	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =12A, dI/dt=100A/μs		22.9		ns	
Reverse Recovery Charge	$Q_{RR}$			18.3		nC	

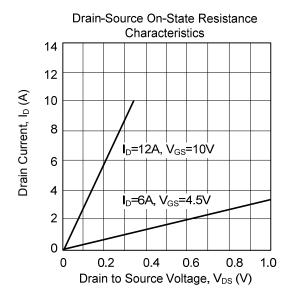
Note: Pulse width ≤300µs, duty cycle≤0.5%.

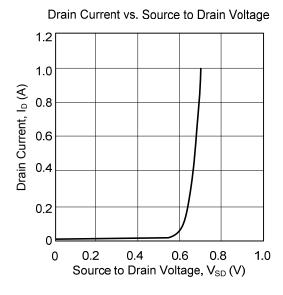
<sup>2.</sup> Pulse width limited by T<sub>J(MAX)</sub>

### ■ TYPICAL CHARACTERISTICS









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